

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SD2553

HORIZONTAL DEFLECTION OUTPUT FOR HIGH RESOLUTION DISPLAY, COLOR TV

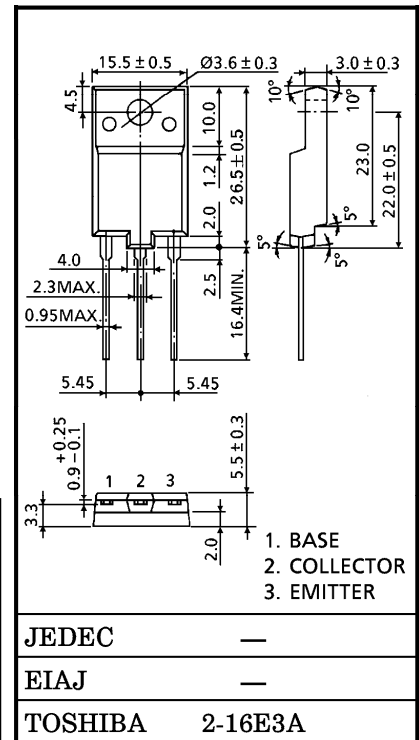
HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CBO} = 1700\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 5\text{ V (Max.)}$
- High Speed : $t_f = 0.3\ \mu\text{s (Typ.)}$
- Built-in Damper Type
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

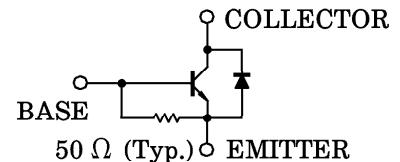
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	1700	V
Collector-Emitter Voltage	V_{CEO}	600	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	DC	I_C	8
	Pulse	I_{CP}	16
Base Current	I_B	4	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	50	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

Unit in mm



Weight : 5.5 g (Typ.)

EQUIVALENT CIRCUIT



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 1700\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	66	—	200	mA
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E = 400\text{ mA}, I_C = 0$	5	—	—	V
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	8	—	28	—
	$h_{FE}(2)$	$V_{CE} = 5\text{ V}, I_C = 6\text{ A}$	5	—	9	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 6\text{ A}, I_B = 1.2\text{ A}$	—	—	5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 6\text{ A}, I_B = 1.2\text{ A}$	—	0.9	1.2	V
Forward Voltage (Damper Diode)	$-V_F$	$I_F = 8\text{ A}$	—	1.6	2.0	V
Transition Frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0,$ $f = 1\text{ MHz}$	—	155	—	pF
Switching Time (Fig.1)	Storage Time	t_{stg}	—	9	12	μs
	Fall Time	t_f		0.3	0.7	

Fig.1 Switching time test circuit

